Amendments to the Claims:

1. (Currently amended) A composition for forming a porous film comprising a condensation product and an organic solvent wherein the condensation product is obtained by hydrolysis and condensation, in the presence of a basic catalyst, of

one or more silane compounds represented by formula (1): $R^1_kSi(OR^2)_{4-k}$

wherein R^1 represents an organic group having 1 to 8 carbons, and when there are two or more R^1s, the R^1s may be independently the same or different; R^2 represents an alkyl group having 1 to 4 carbons, and when there are two or more R^2s, the R^2s may be independently the same or different; and k is an integer from 0 to 3;

and one or more crosslinking agents represented by formla (2):

$\{X_j(Y)_{3-j}Si\text{-}(L)_m\text{-}\}_nMZ_{4-n}$

wherein X represents a hydrogen atom, a halogen atom or an alkoxy group having 1 to 4 carbons; Y represents a hydrogen atom, an alkyl group having 1 to 4 carbons or a phenyl; Z represents a hydrogen atom, a halogen atom, an alkyl group having 1 to 4 carbons, an alkoxy group having 1 to 4 carbons or a phenyl; L represents a linear or branched alkylene group having 1 to 6 carbons, an alkenylene having 1 to 6 carbons, an alkynylene having 1 to 6 carbons or a phenylene group; M represents a carbon atom or a silicon atom; j is an integer from 1 to 3; m is 0 or 1; and n is 3 or 4.

2. (Currently amended) The composition for forming a porous film according to Claim 1 wherein said basic catalyst comprises a ~~is~~ quaternary ammonium hydroxide.

3. (Original) The composition for forming a porous film according to Claim 2 wherein said quaternary ammonium hydroxide is selected from the group consisting of tetramethylammonium hydroxide, choline and tetrapropylammonium hydroxide.

4. (Currently amended) A method for manufacturing a porous film comprising ~~steps of~~ applying a ~~said~~ composition according to ~~any one of~~ Claims 1 ~~to 3~~ on a substrate ~~so as~~ to form a film thereon, drying the film and heating the dried film ~~so as~~ to cure the film.

5. (Currently amended) A porous film comprising a ~~formable by said~~ composition according ~~any one of~~ to Claims 1 ~~to 3~~.

6. (Currently amended) An interlevel insulating film comprising a ~~formable by said~~ composition according to ~~any one of~~ Claims 1 ~~to 3~~.

7. (Currently amended) A semiconductor device comprising a porous film therein, the porous film comprising ~~being formable by~~ a composition comprising a condensation product and an organic solvent wherein the condensation product is obtained by hydrolysis and condensation, in the presence of a basic catalyst, of

one or more silane compounds represented by formula (1): $R^1_kSi(OR^2)_{4-k}$

wherein R^1 represents an organic group having 1 to 8 carbons, and when there are two or more R^1s, the R^1s may be independently the same or different; R^2 represents an alkyl group having 1 to 4 carbons, and when there are two or more R^2s, the R^2s may be independently the same or different; and k is an integer from 0 to 3;

and one or more crosslinking agents represented by formla (2):

$\{X_j(Y)_{3-j}Si\text{-}(L)_m\text{-}\}_nMZ_{4-n}$

wherein X represents a hydrogen atom, a halogen atom or an alkoxy group having 1 to 4 carbons; Y represents a hydrogen atom, an alkyl group having 1 to 4 carbons or a phenyl; Z represents a hydrogen atom, a halogen atom, an alkyl group having 1 to 4 carbons, an alkoxy group having 1 to 4 carbons or a phenyl; L represents a linear or branched alkylene group having 1 to 6 carbons, an alkenylene having 1 to 6 carbons, an alkynylene having 1 to 6 carbons or a phenylene group; M represents a carbon atom or a silicon atom; j is an integer from 1 to 3; m is 0 or 1; and n is 3 or 4.

8. (Currently amended) The semiconductor device according to Claim 7 wherein said basic catalyst comprises a ~~is~~ quaternary ammonium hydroxide.

9. (Currently amended) The semiconductor device according to Claim 8 ~~7~~ wherein said quaternary ammonium hydroxide is selected from the group consisting of tetramethylamonium hydroxide, choline and tetrapropylammonium hydroxide.

10. (Currently amended) The semiconductor device according to ~~any one of~~ Claims 7 ~~to 9~~ wherein said porous film is between metal interconnections in a same layer or multi-level interconnects, or is between upper and lower metal interconnection layers.